



40V PNP LOW VCESAT TRANSISTOR IN PowerDI3333-8

Features

- BV_{CEO} > -40V
- Small Form Factor Thermally Efficient Package.
 Enables Higher Density End Products
- I_C = -2A Continuous Collector Current
- I_{CM} = -3A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} < -320mV @ -1A
- Complementary NPN Type: DXTN22040DFG
- Rated to +175°C Ideal For High Temperature Environment
- Wettable Flank For Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

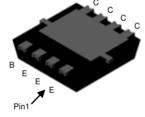
- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.03 grams (Approximate)

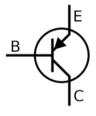
Applications

- High-Side Switch
- Supply Line Switching
- Motor Driving

PowerDI3333-8 (SWP) (Type UX)







Top View Bottom View

Device Symbol

Ordering Information (Note 4)

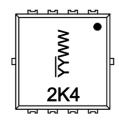
Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
DXTP22040DFG-7	2K4	7	12	2,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

PowerDI3333-8 (SWP) (Type UX)



2K4 = Product Type Marking Code

YYWW = Date Code Marking

YY = Last Two Digits of Year (ex: 19 = 2019)

WW = Week Code (01 to 53)



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Collector-Base Voltage	V _{CBO}	-50	V	
Collector-Emitter Voltage	V _{CEO}	-40	V	
Emitter-Base Voltage	V _{EBO}	-7	V	
Continuous Collector Current	I _C	-2	Α	
Peak Pulse Collector Current	I _{CM}	-3		
Continuous Base Current	I _B	-100	mA	
Peak Pulse Base Current	Івм	-200		

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
	(Note 5)		1.07	W
Power Dissipation	(Note 6)	P _D	2.3	W
	(Note 7)	1	3.4	W
	(Note 5)		140	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)	R _{0JA}	65	°C/W
	(Note 7)		44	°C/W
Thermal Resistance, Junction to Leads (Note 8	$R_{\theta JL}$	11	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C	

ESD Ratings (Note 9)

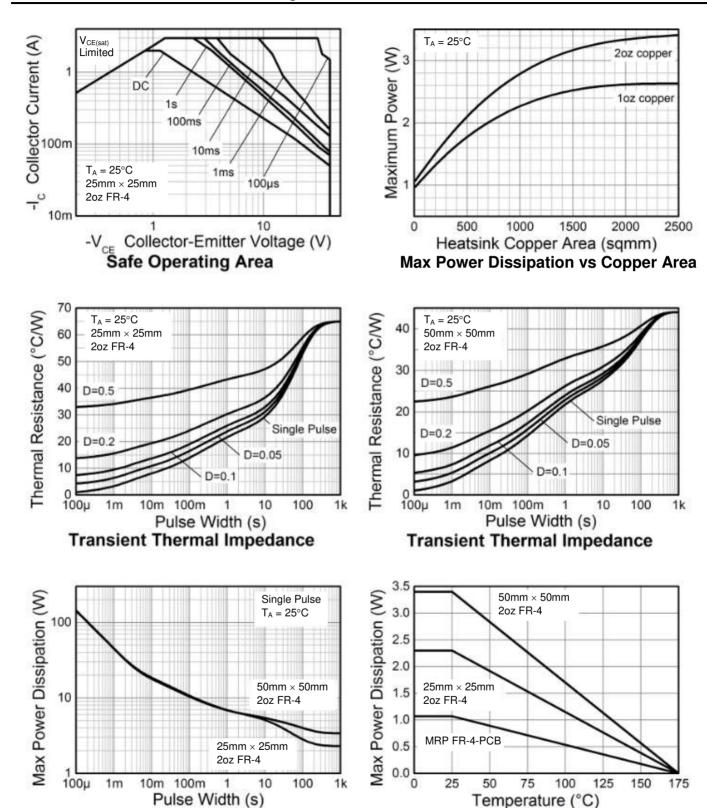
Characteristic	Symbol	Value	Unit	JEDEC Class	
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A	
Electrostatic Discharge – Machine Model	ESD MM	400	V	С	

5. For a device mounted with the collector tab on MRP FR4-PCB; device is measured under still air conditions whilst operating in a steady-state.

- S. To a device mounted with the collector tab on MRP PR4-PCB; device is measl
 Same as Note 5, except the device is mounted on 25mm × 25mm 2oz copper.
 Same as Note 5, except the device is mounted on 50mm × 50mm 2oz copper.
 Thermal resistance from junction to solder-point (at the collector tab).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information



Pulse Power Dissipation

Derating Curve



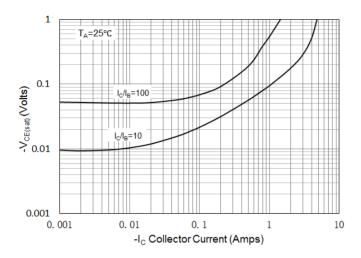
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

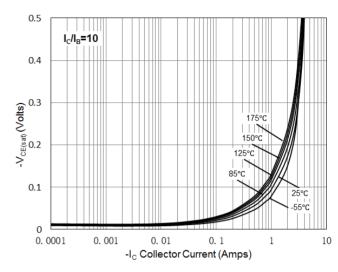
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-50	-71	_	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	-40	-58	_	V	$I_C = -10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.5	_	V	$I_E = -100 \mu A$
Collector-Base Cut-Off Current	I _{CBO}	_	-1 -0.1	-0.1 -20	μΑ	V _{CB} = -50V V _{CB} = -50V, T _A = +150°C
Emitter-Base Cut-Off Current	I _{EBO}	_	-1	-20	nA	V _{EB} = -6V
Collector-Emitter Cut-Off Current	I _{CES}	_	-1	-20	nA	V _{CE} = -40V, V _{BE} = 0V
Static Forward Current Transfer Ratio (Note 10)	h _{FE}	340 300 200 120	410 354 303 203	900 — —		$\begin{split} I_{C} &= -100 \text{mA}, \ V_{CE} = -2 \text{V} \\ I_{C} &= -500 \text{mA}, \ V_{CE} = -2 \text{V} \\ I_{C} &= -1 \text{A}, \ V_{CE} = -2 \text{V} \\ I_{C} &= -2 \text{A}, \ V_{CE} = -2 \text{V} \end{split}$
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(sat)}	_	-56 -48 -81 -146 -218	-140 -170 -320 -400 -600	mV	I _C = -100mA, I _B = -1mA I _C = -500mA, I _B = -50mA I _C = -1A, I _B = -100mA I _C = -2A, I _B = -200mA I _C = -3A, I _B = -300mA
Collector-Emitter Saturation Resistance (Note 10)	R _{CE(sat)}	_	_	320	mΩ	$I_C = -1A$, $I_B = -100mA$
Base-Emitter Saturation Voltage (Note 10)	V _{BE(sat)}	_	-0.88	-1	V	$I_C = -1A$, $I_B = -100mA$
Base-Emitter Turn-On Voltage (Note 10)	$V_{BE(on)}$	_	-0.76	-0.9	V	$I_C = -1A$, $V_{CE} = -2V$
Transition Frequency	f⊤	_	120	_	MHz	$I_{C} = -50 \text{mA}, V_{CE} = -10 \text{V}$ f = 100MHz
Output Capacitance	Cobo	_	12	_	pF	V _{CB} = -10V, f = 1MHz
	t _{delay}	_	10	_	ns	
Switching Characteristics	t _{rise}	_	144	_	ns	$V_{CC} = -10V, I_{C} = -500mA$
Miching Characteristics	tstorage	_	704	_	ns	$I_{B1} = -I_{B2} = -50 \text{mA}$
	t _{fall}	_	48.5	_	ns	

Note: 10. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.

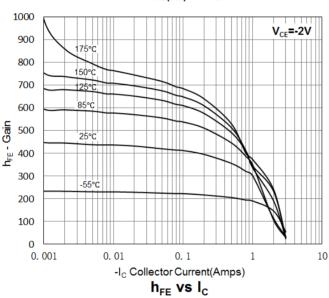


Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

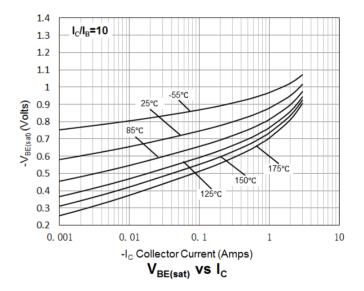


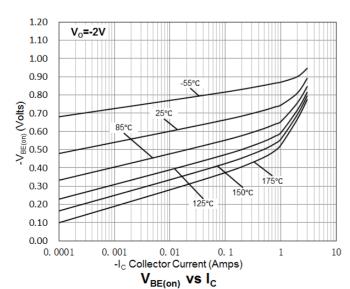










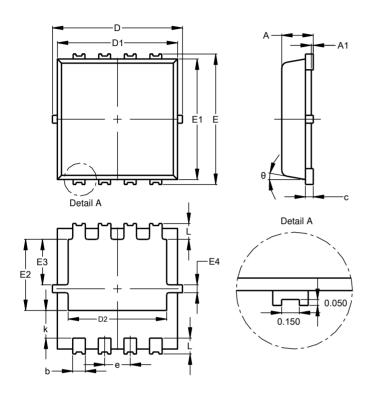




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)

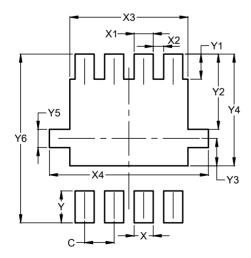


PowerDI3333-8 (SWP)						
(Type UX)						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A 1	0.00	0.05				
b	0.25	0.40	0.32			
С	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	2.30	2.70	2.50			
Е	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E3	0.95	1.35	1.15			
E4	0.10	0.30	0.20			
е	_	_	0.65			
k	0.50	0.90	0.70			
L	0.30	0.50	0.40			
θ	0°	12°	10°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)
С	0.650
X	0.420
X1	0.420
X2	0.230
Х3	2.600
X4	3.500
Υ	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700



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